

Amendments to the Claims

Please amend the claims as follows:

1.-3. (Canceled)

4. (Currently Amended) A method of cleaning a polishing pad surface subsequent to chemical-mechanical polishing (CMP) a wafer surface containing copper (Cu) or a Cu-based alloy, the method comprising applying to the polishing pad surface a cleaning composition comprising:

about 0.1 to about 3.0 wt.% of ethylenediamine;

an acid in an amount such that the composition ~~The method according to claim 1,~~
~~wherein the composition is a solution having a pH of about 8 to about 11; and~~

deionized water.

5. (Canceled)

6. (Currently Amended) The method according to claim 4, comprising applying the solution to a rotating polishing pad at a flow rate of about 100 to about 600 ml/min.

7. (Original) The method according to claim 6, comprising applying the solution to the polishing pad for about 3 seconds to about 20 seconds after conducting CMP on each of a plurality of wafers having a surface comprising Cu or Cu alloy.

8.-14. (Canceled)

15. (Currently Amended) A method comprising:

(a) conducting chemical-mechanical polishing (CMP) on a first wafer surface of a first wafer containing copper (Cu) or a Cu-based alloy on a surface of a polishing pad;

(b) removing the first wafer from the pad;

(c) applying to the polishing pad surface a cleaning composition, wherein the cleaning composition is a solution comprising:

about 0.1 to about 3.0 wt.% of ethylenediamine;

an acid in an amount such that the composition ~~The method according to claim 12, wherein the composition~~ is a solution having a pH of about 8 to about 11; and deionized water;

(d) rinsing the polishing pad surface with water to remove any cleaning composition on the polishing surface;

(e) conducting CMP on a second wafer; and then

(f) repeating (b) through (e).

16. (Canceled)

17. (Original) The method according to claim 15, comprising applying the solution to a rotating polishing pad at a flow rate of about 100 to about 600 ml/min.

18. (Original) The method according to claim 17, comprising applying the composition to the rotating polishing pad for about 3 seconds to about 20 seconds.

19-27. (Canceled)

28. (Currently Amended) A method of cleaning a surface of a polishing pad, comprising:

conducting chemical-mechanical polishing (CMP) on a first wafer on the surface of the polishing pad;

removing the first wafer from the polishing pad;

applying to the polishing pad surface a cleaning composition, wherein the cleaning composition is a solution comprising:

about 0.1 to about 3.0 wt.% of ethylenediamine;

an acid in an amount such that the composition ~~The method according to claim 26, wherein the cleaning composition~~ is a solution having a pH of about 8 to about 11; and

deionized water; and
cleaning the polishing pad surface with the cleaning composition.

29.-33. (Canceled)